HFZT

SCS306AM

SiC Schottky Barrier Diode

VOLTAGE RANGE: 650V

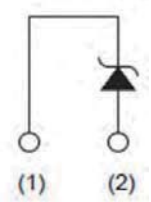
Features

- Shorter recove time
- Reduced tperature dependence
- High-speeditching possible
- High surge current capabili

MECHANICAL DATA

- Case style:TO-220 molded plastic
- Mounting position:any
- Silicon carbide epitaxial planar type

●Inner circuit



(1) Cathode
(2) Anode

●Packaging specifications

Type	Packaging	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	50
	Packing code	C
	Marking	SCS306AM

MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V_{RM}	650	V
Reverse voltage (DC)		V_R	650	V
Continuous forward current (T_c= 120°C)		I_F	6	A
Surge non-repetitive forward current	PW=10ms sinusoidal, T_j=25°C	I_{FSM}	47	A
	PW=10ms sinusoidal, T_j=150°C		40	A
	PW=10μs square, T_j=25°C		170	A
Repetitive peak forward current		I_{FRM}	22 *1	A
i^2t value	1≦PW≦10ms, T_j=25°C	$\int i^2dt$	11	A^2s
	1≦PW≦10ms, T_j=150°C		8.0	A^2s
Total power disspation		P_D	30 *2	W
Junction temperature		T_j	175	°C
Range of storage temperature		T_{stg}	−55 to +175	°C

*1 T_c=100°C, T_j=150°C, Duty cycle=10% *2 T_c=25°C

RATINGS AND CHARACTERISTIC CURVES

Electrical Specification (T_A=25°C unless otherwise specified)

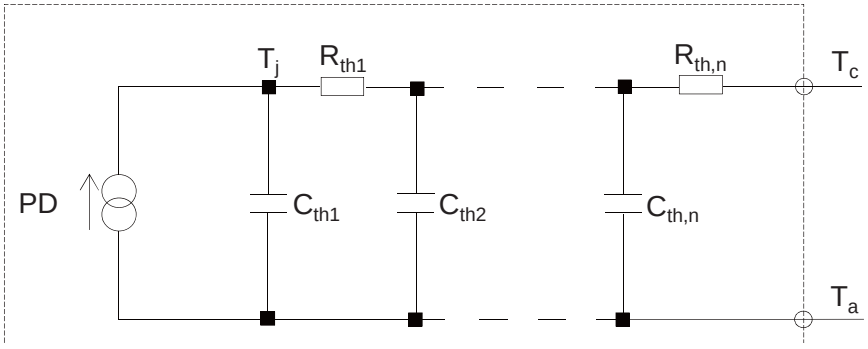
●Electrical characteristics (T_j = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	I_F=6A,T_j=25°C	-	1.35	1.50	V
		I_F=6A,T_j=150°C	-	1.44	1.71	V
		I_F=6A,T_j=175°C	-	1.50	-	V
Reverse current	I_R	V_R=650V,T_j=25°C	-	0.018	30	μA
		V_R=650V,T_j=150°C	-	1.2	120	μA
		V_R=650V,T_j=175°C	-	3.6	-	μA
Total capacitance	C	V_R=1V,f=1MHz	-	300	-	pF
		V_R=650V,f=1MHz	-	27	-	pF
Total capacitive charge	Q_C	V_R=400V,di/dt=350A/μs	-	19	-	nC
Switching time	t_C	V_R=400V,di/dt=350A/μs	-	15	-	ns
Non-repetetive Avaranche Energy	E_{ava}	L=1mH	-	71	-	mJ
Thermal resistance	$R_{th(j-c)}$	-	-	4.2	4.9	°C/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	4.19E-01	K/W
R_{th2}	1.64E+00	
R_{th3}	2.13E+00	

Symbol	Value	Unit
C_{th1}	3.12E-04	Ws/K
C_{th2}	1.71E-03	
C_{th3}	3.97E-01	



RATINGS AND CHARACTERISTIC CURVES

Fig.1 V_F - I_F Characteristics

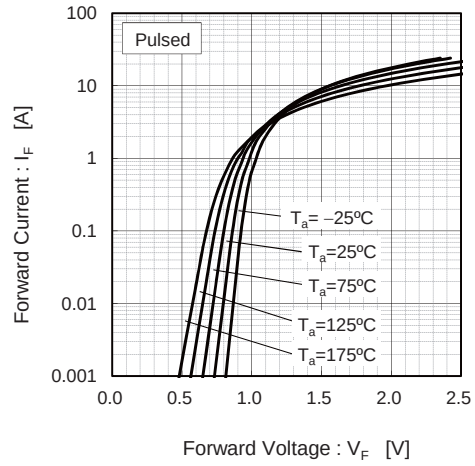


Fig.2 V_F - I_F Characteristics

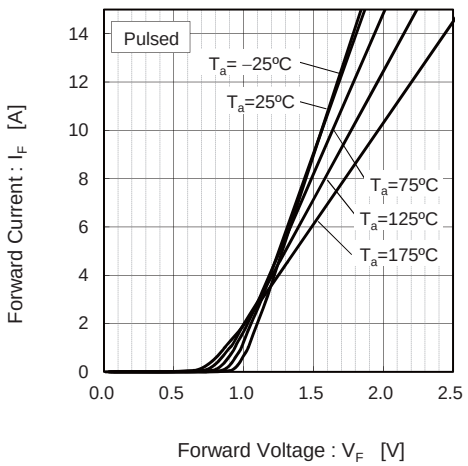


Fig.3 V_R - I_R Characteristics

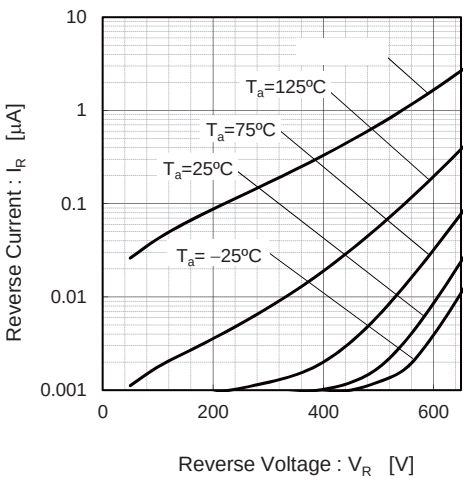


Fig.4 V_R-C_t Characteristics

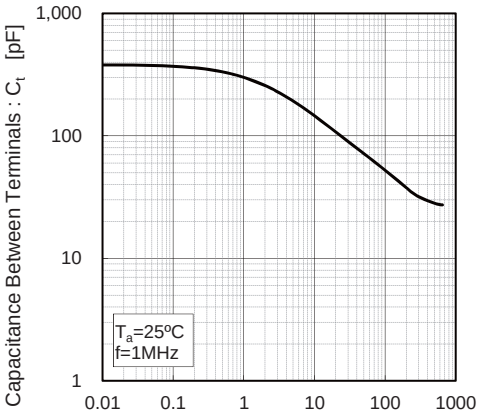


Fig.5 Typical Transient Thermal Resistance vs. Pulse Width

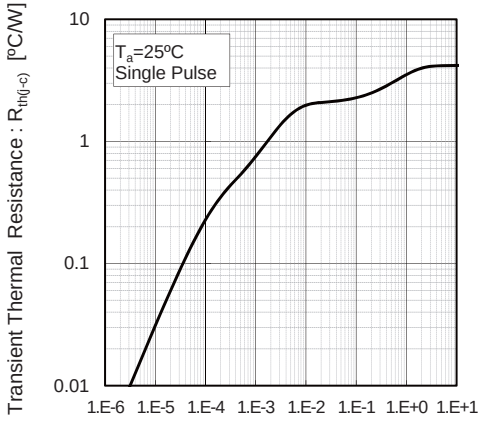


Fig.6 Power Dissipation

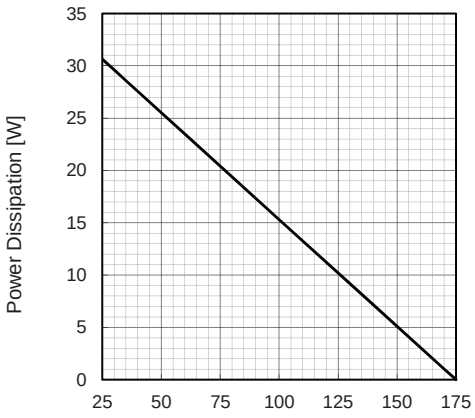
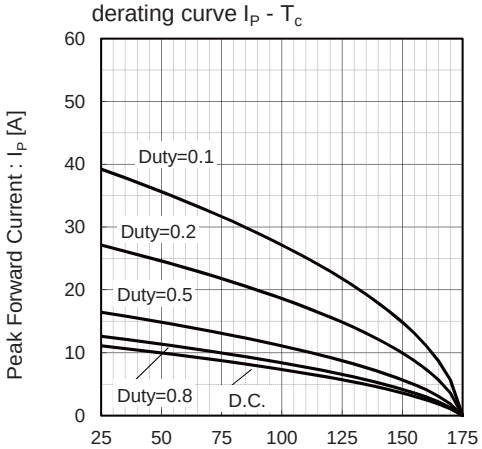
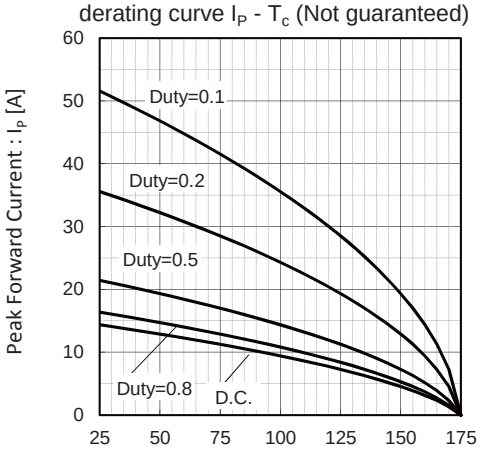


Fig.7*3 Maximum peak forward current derating curve I_P - T_c



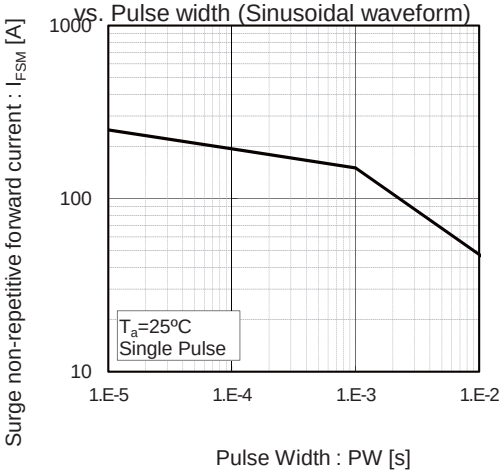
*3 Based on max Vf, max $R_{th(j-c)}$
Valid for switching of above 10kHz,

Fig.8*4 Typical peak forward current derating curve I_P - T_c (Not guaranteed)



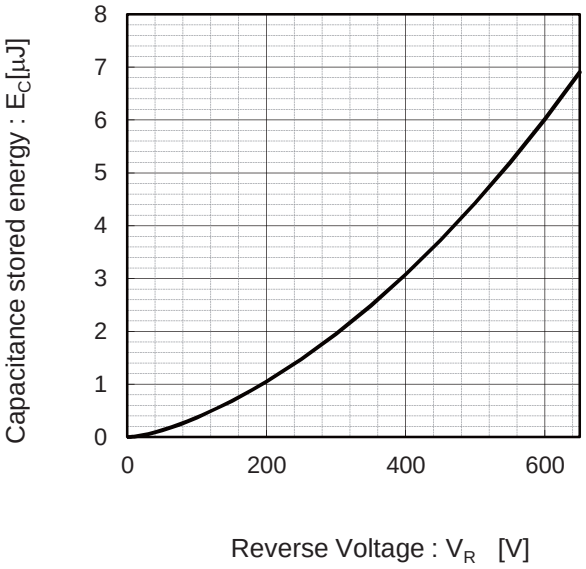
*4 Based on typ Vf, typ $R_{th(j-c)}$
Typical value, not guaranteed

Fig.9 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)



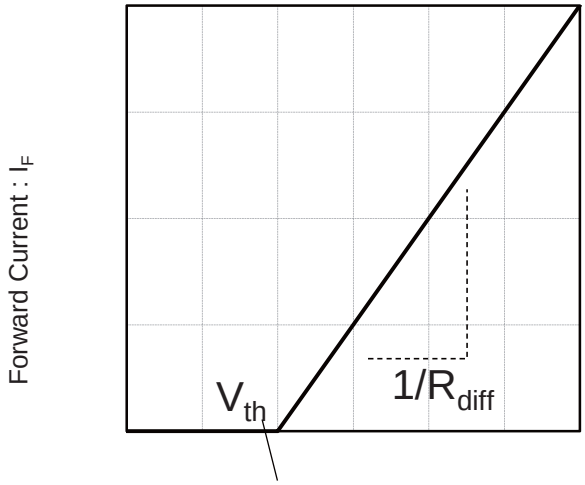
RATINGS AND CHARACTERISTIC CURVES

Fig.10 Typical capacitance store energy



●Symplified forward characteristic model

Fig.11 Equivalent forward current curve



$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th}(T_j) = a_0 + a_1 T_j$$
$$R_{diff}(T_j) = b_0 + b_1 T_j + b_2 T_j^2$$

Symbol	Typical Value	Unit
a_0	9.66E-01	V
a_1	-1.10E-03	V/°C
b_0	5.87E-02	Ω
b_1	1.24E-04	Ω/°C
b_2	1.28E-06	Ω/°C^2

T_j in ºC; -55 ºC < T_j < 175ºC ; I_F < 12 A